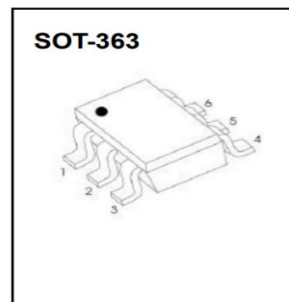
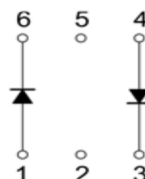


Silicon Epitaxial Planar Diodes High Voltage Switching Diode

Features

- Fast switching speed
- Surface mount package ideally suited for automatic insertion

	BAS19DW	BAS20DW	BAS21DW
MARKING	JP	JR	JS



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	V
BAS19DW		200	
BAS20DW		250	
Reverse Voltage	V_R	100	V
BAS19DW		150	
BAS20DW		200	
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Forward Continuous Current	I_{FM}	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	2.5	A
at $t = 1\text{ ms}$		0.5	
Power Dissipation	P_d	250	mW
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V_F	-	1	V
at $I_F = 100\text{ mA}$		-	1.25	
at $I_F = 200\text{ mA}$		-	-	
Reverse Breakdown Voltage	$V_{(BR)R}$	120	-	V
at $I_R = 100\text{ }\mu\text{A}$		200	-	
BAS19DW		250	-	
Reverse Current	I_R	-	100	nA
at $V_R = 100\text{ V}$		-	100	
at $V_R = 150\text{ V}$		-	100	
at $V_R = 200\text{ V}$		-	100	
Total Capacitance	C_T	-	5	pF
at $V_R = 0, f = 1\text{ MHz}$				
Reverse Recovery Time	t_{rr}	-	50	ns
at $I_F = I_R = 30\text{ mA}, I_{rr} = 0.1I_R, R_L = 100\text{ }\Omega$				

